

# ZXTN5551Z 160V, SOT89, NPN high voltage transistor

# Summary

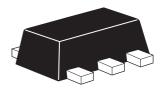
**BV<sub>CEO</sub> > 160V** 

 $BV_{EBO} > 6V$ 

 $I_{C(cont)} = 600 mA$ 

 $P_{D} = 1.2W$ 

Complementary part number ZXTP5401Z

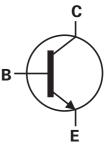


# **Description**

A high voltage NPN transistor in a small outline surface mount package

## **Features**

- 160V rating
- SOT89 package

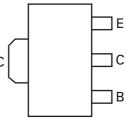


# **Applications**

· High voltage amplification

# **Ordering information**

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN5551ZTA	7	12	1000



Pinout - top view

## **Device marking**

N51

# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	180	V
Collector-emitter voltage	V <sub>CEO</sub>	160	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Continuous collector current <sup>(a)</sup>	I <sub>C</sub>	600	mA
Power dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1.2	W
Linear derating factor		9.6	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

# Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	104	°C/W

## NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated).

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	180	270		V	I <sub>C</sub> = 100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	160	200		V	I <sub>C</sub> = 1mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	7.85		V	I <sub>E</sub> = 10μA
Collector cut-off current	I <sub>CBO</sub>		<1	50	nA	V <sub>CB</sub> = 120V
				50	μΑ	$V_{CB} = 120V, T_{amb} = 100^{\circ}C$
Collector-emitter	V <sub>CE(sat)</sub>		65	150	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA <sup>(*)</sup>
saturation voltage			115	200	mV	$I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$
Base-emitter saturation	V <sub>BE(sat)</sub>		760	1000	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA <sup>(*)</sup>
voltage			840	1200	mV	$I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$
Static forward current	h <sub>FE</sub>	80	130			$I_C = 1mA, V_{CE} = 5V^{(*)}$
transfer ratio		80	145	250		$I_C = 10 \text{mA}, V_{CE} = 5V^{(*)}$
		30	65			$I_C = 50 \text{mA}, V_{CE} = 5V^{(*)}$
Transition frequency	f <sub>T</sub>		130		MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V f = 100MHz
Output capacitance	C <sub>OBO</sub>			6	pF	V <sub>CB</sub> = 10V, f = 1MHz <sup>(*)</sup>
Small signal	h <sub>FE</sub>	50		260		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V, f=1kHz <sup>(†)</sup>
Delay time	t <sub>(d)</sub>		95		ns	V <sub>CC</sub> = 10V. I <sub>C</sub> = 10mA,
Rise time	t <sub>(r)</sub>		64		ns	$I_{B1} = I_{B2} = 1mA.$
Storage time	t <sub>(s)</sub>		1256		ns	
Fall time	t <sub>(f)</sub>		140		ns	

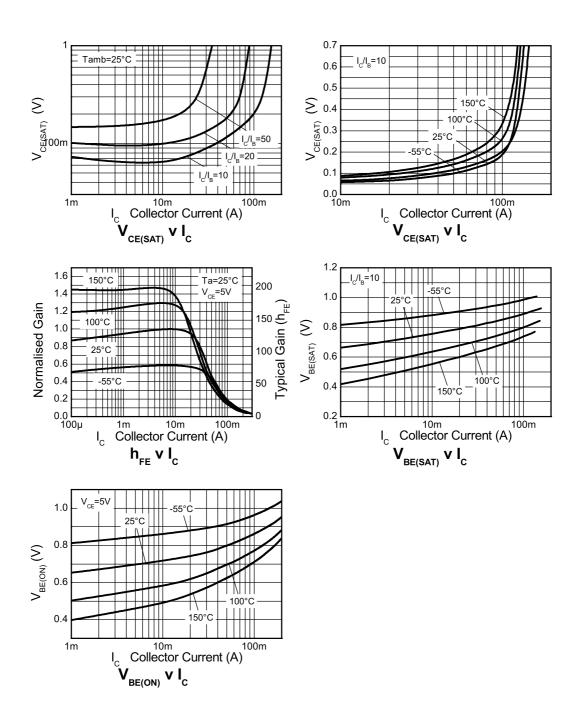
### NOTES:

<sup>(\*)</sup> Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ ; duty cycle  $\leq 2\%$ .

<sup>(†)</sup> Periodic sample test only



# **Typical characteristics**



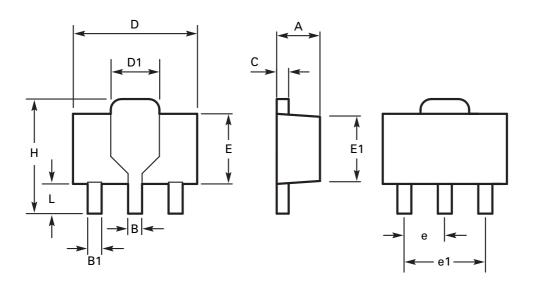
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# Package outline - SOT89



DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	Е	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50 BSC		0.059 BSC	
С	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118	BSC
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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